

BCR8PM-14LD

Triac

Medium Power Use

REJ03G1565-0100 Rev.1.00 Jul 06, 2007

Features

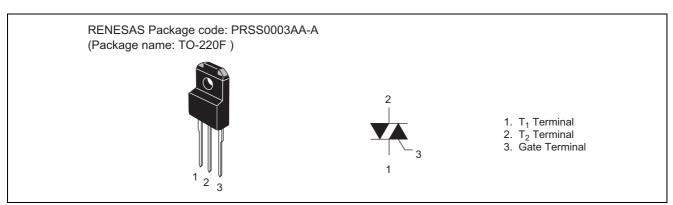
 $\begin{array}{ll} \bullet & I_{T \, (RMS)} : 8 \; A \\ \bullet & V_{DRM} : 700 \; V \end{array}$

• I_{FGTI} , I_{RGTI} , I_{RGTIII} : 50 mA

• Viso : 2000 V

- The product guaranteed maximum junction temperature 150°C.
- Insulated Type
- Planar Type

Outline



Applications

Motor control, heater control

Maximum Ratings

Parameter	Symbol	Voltage class	Unit	
- aramoto	-	14	5	
Repetitive peak off-state voltage ^{Note1}	V_{DRM}	700	V	
Non-repetitive peak off-state voltage ^{Note1}	V_{DSM}	800	V	

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Parameter	Symbol	Ratings	Unit	Conditions
RMS on-state current	I _{T (RMS)}	8	А	Commercial frequency, sine full wave 360° conduction, Tc = 85°C
Surge on-state current	I _{TSM}	48	А	60Hz sinewave 1 full cycle, peak value, non-repetitive
I ² t for fusing	l ² t	9.5	A ² s	Value corresponding to 1 cycle of half wave 60Hz, surge on-state current
Peak gate power dissipation	P_{GM}	5	W	
Average gate power dissipation	P _{G (AV)}	0.5	W	
Peak gate voltage	V_{GM}	10	V	
Peak gate current	I_{GM}	2	Α	
Junction temperature	Tj	- 40 to +150	°C	
Storage temperature	Tstg	- 40 to +150	°C	
Mass	_	2.0	g	Typical value
Isolation voltage	Viso	2000	V	Ta = 25°C, AC 1 minute, $T_1 \cdot T_2 \cdot G$ terminal to case

Notes: 1. Gate open.

Electrical Characteristics

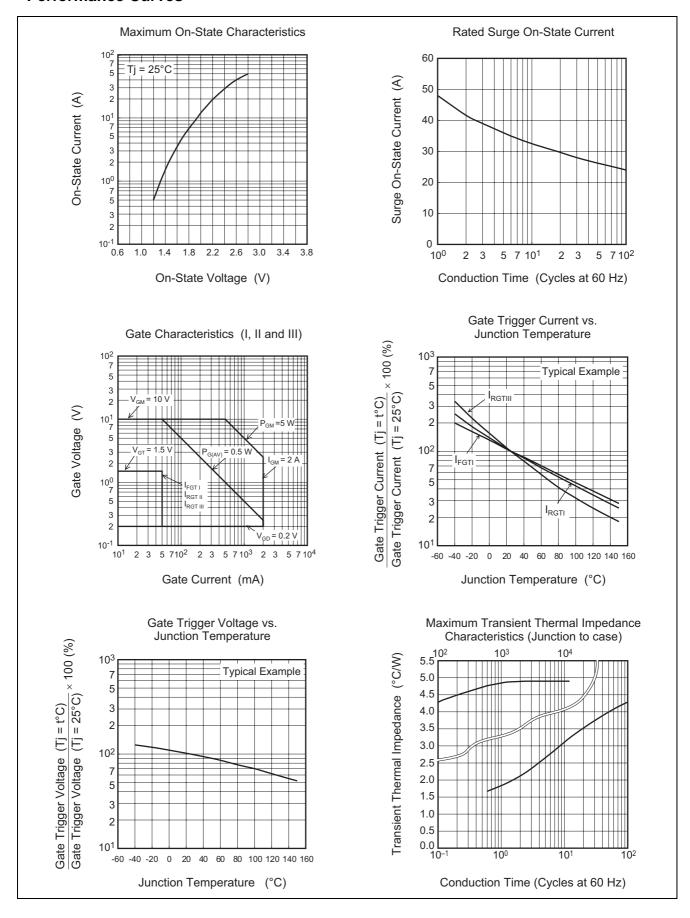
Parameter		Symbol	Min.	Тур.	Max.	Unit	Test conditions
Repetitive peak off-state current		I _{DRM}	_	_	2.0	mA	Tj = 125°C, V _{DRM} applied
On-state voltage		V_{TM}	_	_	2.0	V	Tc = 25°C, I _{TM} = 12 A,
							Instantaneous measurement
Gate trigger voltage ^{Note2}	I	V_{FGTI}		_	1.5	V	$Tj = 25^{\circ}C, V_D = 6 V, R_L = 6 \Omega,$
	II	V_{RGTI}	_	_	1.5	V	$R_G = 330 \Omega$
	III	V_{RGTIII}	_	_	1.5	V	
Gate trigger current ^{Note2}	I	I_{FGTI}	_	_	50	mA	$Tj = 25^{\circ}C, V_D = 6 V, R_L = 6 \Omega,$
	II	I_{RGTI}		_	50	mA	$R_G = 330 \Omega$
	III	I _{RGTIII}	_	_	50	mA	
Gate non-trigger voltage		V_{GD}	0.2	_	_	V	$Tj = 125^{\circ}C, V_D = 1/2 V_{DRM}$
Thermal resistance		R _{th (j-c)}	_	_	4.9	°C/W	Junction to case ^{Note3}
Critical-rate of rise of off-state commutating voltage ^{Note4}		(dv/dt)c	10	_	_	V/μs	Tj = 125°C

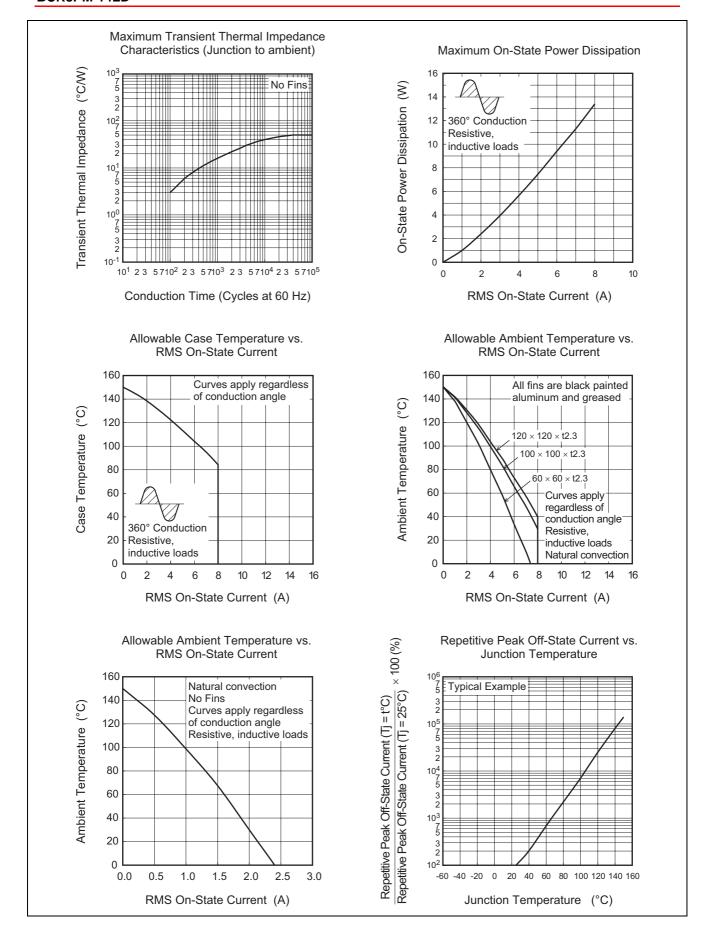
Notes: 2. Measurement using the gate trigger characteristics measurement circuit.

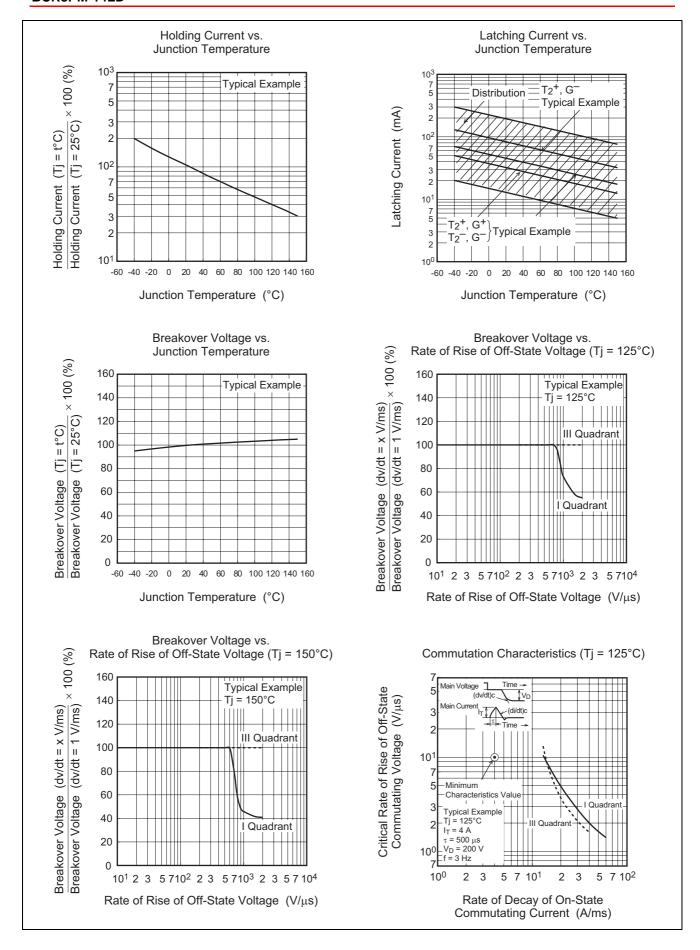
- 3. The contact thermal resistance $R_{\text{th (c-f)}}$ in case of greasing is 0.5°C/W.
- 4. Test conditions of the critical-rate of rise of off-state commutating voltage is shown in the table below.

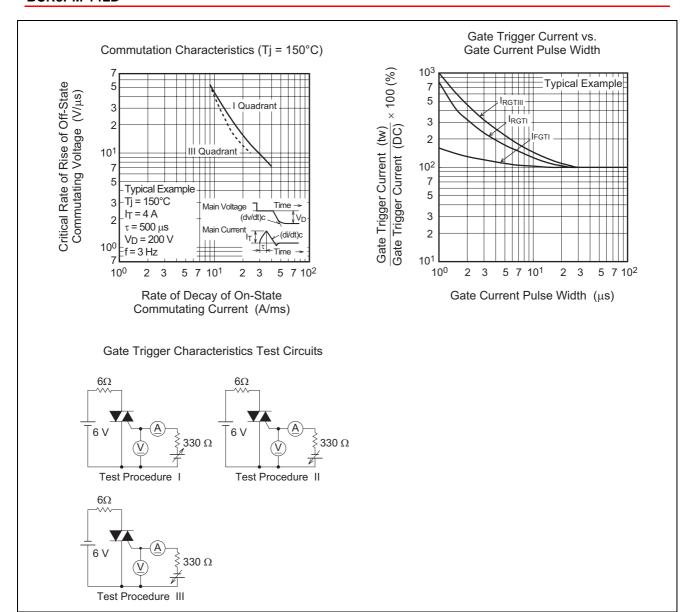
Test conditions	Commutating voltage and current waveforms (inductive load)		
1. Junction temperature Tj = 125°C	Supply Voltage → Time		
2. Rate of decay of on-state commutating current (di/dt)c = - 4 A/ms	Main Current — (di/dt)c — Time		
3. Peak off-state voltage V _D = 400 V	Main Voltage Time		

Performance Curves

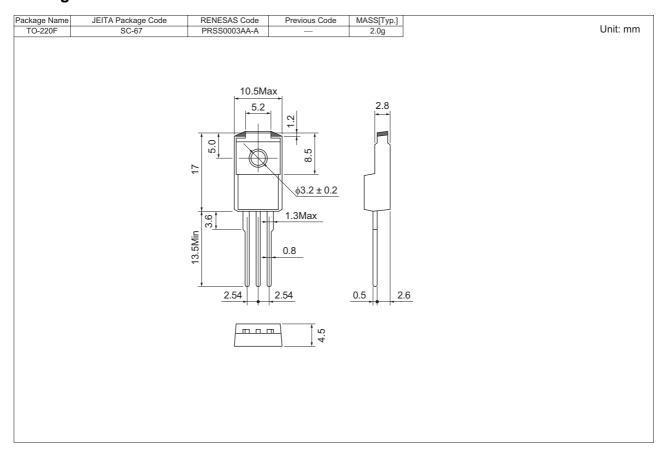








Package Dimensions



Order Code

Lead form	Standard packing	Quantity	Standard order code	Standard order code example
Straight type	Vinyl sack	100	Type name	BCR8PM-14LD
Lead form	Plastic Magazine (Tube)	50	Type name – Lead forming code	BCR8PM-14LD-A8

Note: Please confirm the specification about the shipping in detail.

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